2SC1226, 2SC1226A

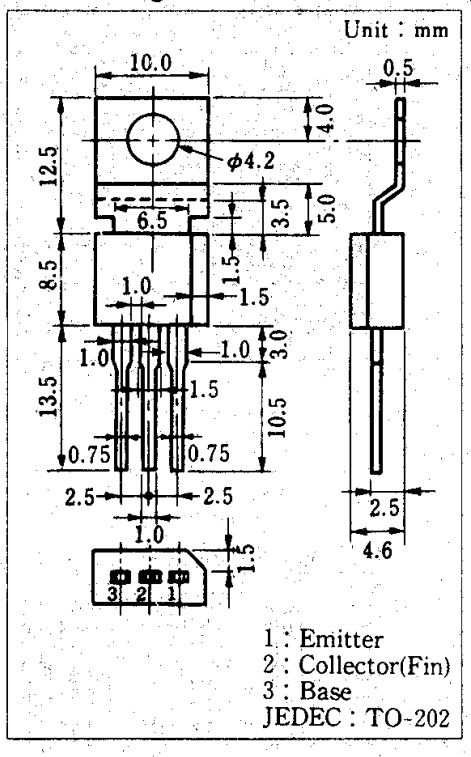
Silicon NPN Epitaxial Planar Type

Medium Power Amplifier
Complementary Pair with 2SA699, 2SA699A

■ Feature

- 5W output in complementary pair with 2SA699, 2SA699A

■ Package Dimensions



1 : Emitter
2 : Collector(Fin)
3 : Base
JEDEC : TO-202

■ Absolute Maximum Ratings (Ta=25°C)

Item		Symbol	Value	Unit
Collector-base voltage	2SC1226	V_{CBO}	40	V
	2SC1226A		50	
Collector-emitter voltage	2SC1226	V_{CEO}	32	V
	2SC1226A		40	
Emitter-base voltage		V_{EBO}	5	V
Peak collector current		I_{CP}	3	A
Base current		I_B	0.6	A
Collector power dissipation (Tc=25°C)		P_C	10	W
Junction temperature		T_j	150	°C
Storage temperature		T_{stg}	−55～+150	°C

■ Electrical Characteristics (Tc=25°C)

Item		Symbol	Condition	min.	typ.	max.	Unit
Collector cutoff current		I_{CBO}	V_{CB}=20 V, I_E=0			1	μA
		I_{CEO}	V_{CE}=12 V, I_B=0			100	
Emitter cutoff current		I_{EBO}	V_{EB}=5 V, I_C=0			100	μA
Collector-base voltage	2SC1226	V_{CBO}	I_C=1 mA, I_E=0	40			V
	2SC1226A			50			
Collector-emitter voltage	2SC1226	V_{CEO}	I_C=10 mA, I_B=0	32			V
	2SC1226A			40			
DC current gain		h_{FE}*1	V_{CE}=5V, I_C=1 A*2	50	120	220	
Transition frequency		f_T	V_{CE}=5 V, I_C=0.5 A*2		150		MHz
Base-emitter saturation voltage		$V_{BE(sat)}$	I_C=2 A, I_B=0.2 A*2			1.5	V
Collector-emitter saturation voltage		$V_{CE(sat)}$	I_C=2 A, I_B=0.2 A*2		0.4	1	V
Collector output capacitance		C_{ob}	V_{CB}=5 V, I_E=0, f=1 MHz		50		pF

*2 パルス測定

h_{FE} Classifications

Class	P	Q	R
h_{FE}	50～100	80～160	120～220